

## NCE N-Channel Enhancement Mode Power MOSFET



The NCE30H15 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## **General Features**

- V<sub>DS</sub> =30V,I<sub>D</sub> =150A
  R<sub>DS(ON)</sub> <3.0 mΩ @ V<sub>GS</sub>=10V
  R<sub>DS(ON)</sub> <4.0mΩ @ V<sub>GS</sub>=4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

## Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

## 100% UIS TESTED!

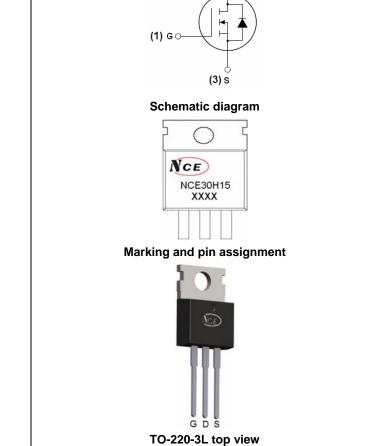
## 100% ΔVds TESTED!

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30H15	NCE30H15	TO-220-3L	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	150	А
Drain Current-Continuous(Tc=100℃)	I <sub>D</sub> (100℃)	105	A
Pulsed Drain Current	I <sub>DM</sub>	600	A
Maximum Power Dissipation	PD	130	W
Derating factor		0.87	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1700	mJ
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C



(2) D





NCE30H15

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>ejc</sub>	1.15	°C/W	l
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## Electrical Characteristics (T<sub>C</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter Symbol		Condition	Min	Тур	Max	Unit	
Off Characteristics	·			•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA		35	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics (Note 3)	·			•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	1.2	1.7	2.5	V	
		V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	2.3	3.0	mΩ	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		3.2	4.0		
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	32	-	-	S	
Dynamic Characteristics (Note4)	·			•			
Input Capacitance	C <sub>lss</sub>		-	5000	-	PF	
Output Capacitance	Coss	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V, F=1.0MHz	-	1135	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	563	-	PF	
Switching Characteristics (Note 4)	·			•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	26	-	nS	
Turn-on Rise Time	tr	V <sub>DD</sub> =15V,I <sub>D</sub> =2A,R <sub>L</sub> =15Ω	-	24	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =10V,R <sub>G</sub> =2.5Ω	-	91	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	39	-	nS	
Total Gate Charge	Qg	N/ 45//1 00A	-	38		nC	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =15V,I <sub>D</sub> =30A, V <sub>GS</sub> =10V	-	9		nC	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	13		nC	
Drain-Source Diode Characteristics			•			•	
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =150A	-		1.2	V	
Diode Forward Current (Note 2)	Is		-	-	150	Α	
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 20A	-	42	-	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	39	_	nC	
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD					

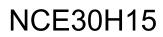
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. E\_{AS} condition : Tj=25  $^\circ \!\! C$  ,V\_{DD}=20V,V\_G=10V,L=1mH,Rg=25\Omega , I\_{AS}=58.5A

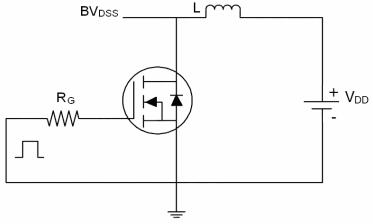


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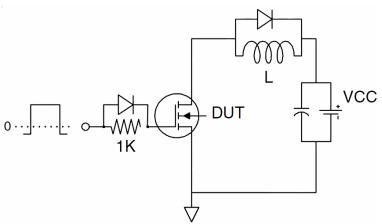
Pb Free Product



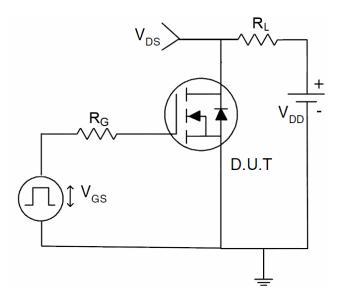
## Test circuit 1) E<sub>AS</sub> Test Circuit



## 2) Gate Charge Test Circuit



3) Switch Time Test Circuit



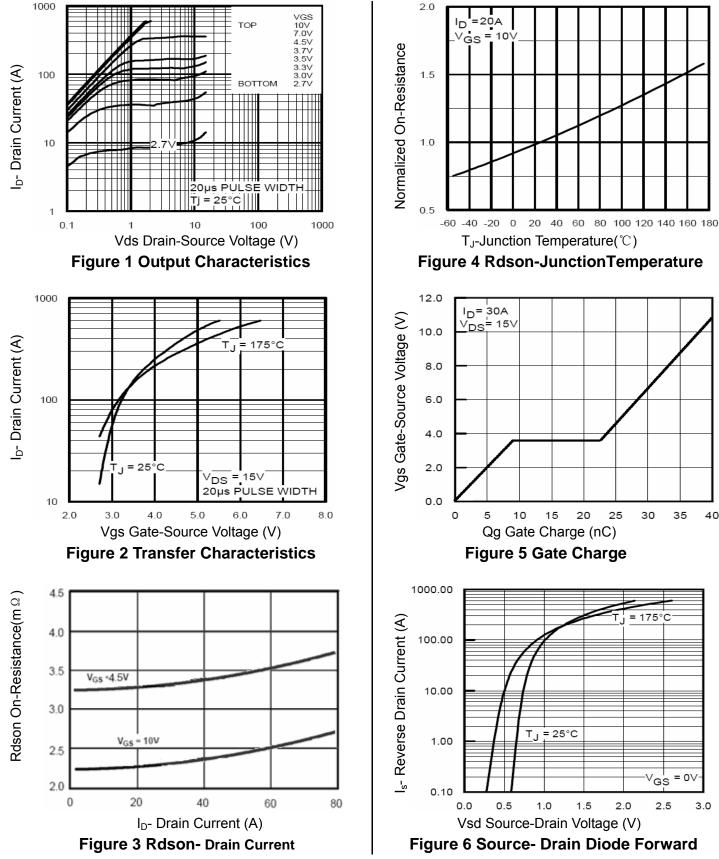


30

35

40





= 0\ Vgs

3.0

2.5



10

1

0.1

Tc = 25°C

Tj = 175°C Single Pulse

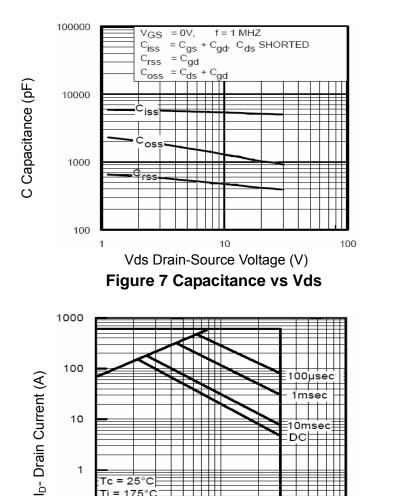
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10mse 

100



# NCE30H15



10

Vds Drain-Source Voltage (V)

**Figure 8 Safe Operation Area** 

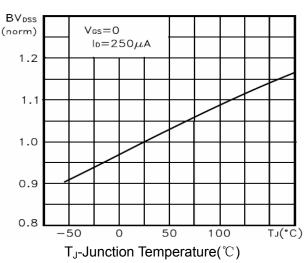


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

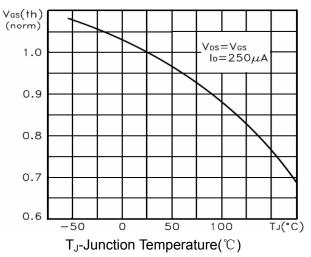


Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

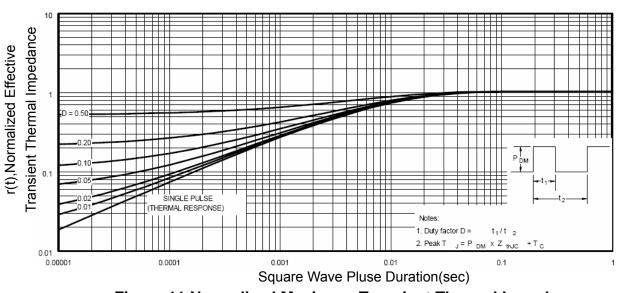


Figure 11 Normalized Maximum Transient Thermal Impedance

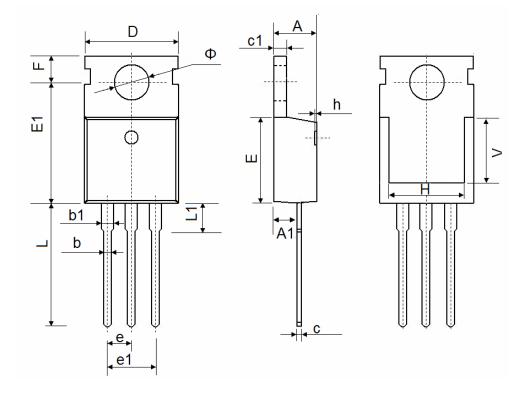


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# NCE30H15

## TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	







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